

MDL-III-852L/1~30mW

### INFRARED DIODE LASER AT 852nm

Diode infrared laser module at 852nm is made features of ultra compact, long lifetime, low cost and easy operating, which is used in measurement, communication, spectrum analysis, etc.



### SPECIFICATIONS

Wavelength (nm)	852±10	
Operating mode	CW	
Output power (mW)	>1, 5, 10, ..., 30	
Power stability (rms, over 4 hours)	<1%, <3%, <5%	
Transverse mode	Near TEM <sub>00</sub>	
Dimensions of beam at the aperture (1/e <sup>2</sup> ,mm)	~4.0	
Beam divergence, full angle (mrad)	<1.0	
Polarization ratio	>50:1 (>100:1, optional) Horizontal±5 degree (Vertical Optional)	
Warm-up time (minutes)	<5	
Pointing stability after warm-up (mrad)	<0.05	
Beam height from base plate (mm)	24.8	
Operating temperature (°C)	10~35	
Power supply (85-264VAC)	PSU-III-LED	PSU-III-FDA
TTL / Analog modulation	TTL or Analog with 1Hz-1KHz 1KHz-10KHz, 10KHz-30KHz optional	
Expected lifetime (hours)	10000	
Warranty	1 year	

